



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

MPSA55

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

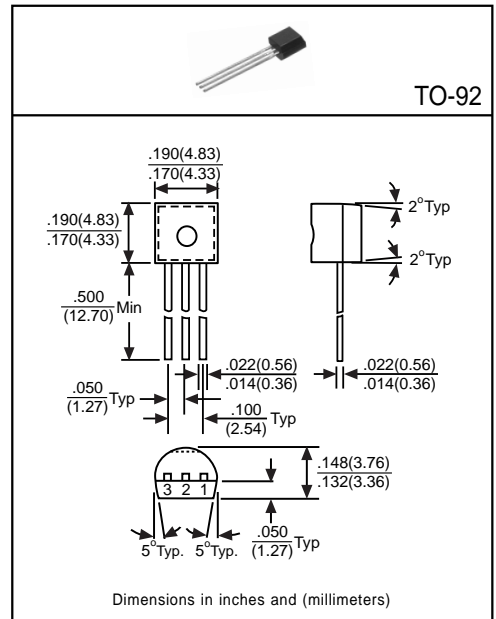
Designed for general purpose amplifier applications.

Pinning

- 1 = Emitter
- 2 = Base
- 3 = Collector

Absolute Maximum Ratings (TA=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-60	V
Collector-Emitter Voltage	VCEO	-60	V
Emitter-Base Voltage	VEBO	-4	V
Collector Current	IC	-500	mA
Total Power Dissipation	PD	625	mW
Junction Temperature	TJ	+150	°C
Storage Temperature	TSTG	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVCBO	-60	-	-	V	IC=-100μA, IE=0
Collector-Emitter Breakdown Voltage	BVCEO	-60	-	-	V	IC=-1mA, IB=0
Emitter-Base Breakdown Voltage	BVEBO	-4	-	-	V	IE=-100μA, IC=0
Collector Cutoff Current	ICBO	-	-	-0.1	μA	VCB=-60V, IE=0
	ICEO	-	-	-0.1	μA	VCE=-60V, IB=0
Collector-Emitter Saturation Voltage <sup>(1)</sup>	VCE(sat)	-	-	-0.25	V	IC=-100mA, IB=-10mA
Base-Emitter On Voltage <sup>(1)</sup>	VBE(on)	-	-	-1.2	V	IC=-100mA, VCE=-1V
DC Current Gain <sup>(1)</sup>	hFE1	50	-	-	-	IC=-10mA, VCE=-1V
	hFE2	50	-	-	-	IC=-100mA, VCE=-1V
Transition Frequency	fT	50	-	-	MHz	IC=-100mA, VCE=-1V, f=1MHz

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%